GAN 2811

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#2 Prior Art
FJONES
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To: Commissioner of Patents and Trademarks
Washington, D.C. 20231

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Subject: Serial No. 09/898,386 07/05/01

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DIODE FOR POWER PROTECTION

Grp. Art Unit: 2811

INFORMATION DISCLOSURE STATEMENT

Enclosed is Form PTO-1449, Information Disclosure Citation In An Application.

The following Patents and/or Publications are submitted to comply with the duty of disclosure under CFR 1.97-1.99 and 37 CFR 1.56. Copies of each document is included herewith.

U.S. Patent 6,002,568 to Ker et al., "ESD Protection Scheme for Mixed-Voltage CMOS Integrated Circuits," discloses an ESD circuit using silicon controlled rectifier (SCR) devices.

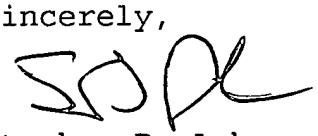
U.S. Patent 5,898,205 to Lee, "Enhanced ESD Protection Circuitry," teaches an ESD protection circuit where conventional CMOS protection transistors are capacitively-coupled to improve performance.

U.S. Patent 6,011,681 to Ker et al., "Whole-Chip ESD Protection for CMOS ICS Using Bi-Directional SCRS," discloses a circuit using bi-directional SCR devices to provide current discharge paths between separate power supplies.

U.S. Patent 5,530,612 to Maloney, "Electrostatic Discharge Protection Circuits Using Biased and Terminated PNP Transistor Chains," teaches ESD protection circuits using biased diode strings and cantilevered diode strings.

U.S. Patent 5,747,834 to Chen et al., "Adjustable Bipolar SCR Holding Voltage for ESD Protection Circuits in High Speed Bipolar/BiCMOS Circuits," discloses a bipolar SCR with an adjustable holding voltage wherein the device is entirely constructed in an n-well and uses a buried layer.

Sincerely,



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